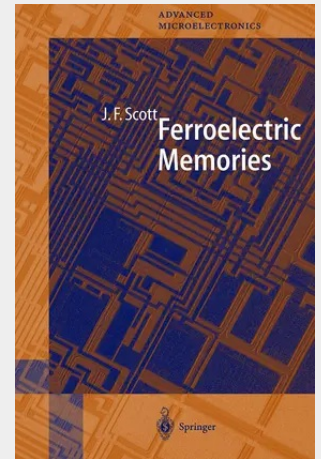


Scott

Ferroelectric Memories

Ferroelectric memories have changed in 10 short years from academic curiosities of the university research labs to commercial devices in large-scale production. This is the first text on ferroelectric memories that is not just an edited collection of papers by different authors. Intended for applied physicists, electrical engineers, materials scientists and ceramists, it includes ferroelectric fundamentals, especially for thin films, circuit diagrams and processing chapters, but emphasises device physics. Breakdown mechanisms, switching kinetics and leakage current mechanisms have lengthy chapters devoted to them. The book will be welcomed by research scientists in industry and government laboratories and in universities. It also contains 76 problems for students, making it particularly useful as a textbook for fourth-year undergraduate or first-year graduate students.

The book gives a comprehensive introduction to the field by an established expert on ferroelectric memories



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